



**UPO**

UNIVERSITÀ DEL PIEMONTE ORIENTALE  
DIPARTIMENTO DI SCIENZE E INNOVAZIONE TECNOLOGICA

## EVENTI DiSIT

Seminario | Seminar

20-07-2023

11:00-12:00

Aula 207

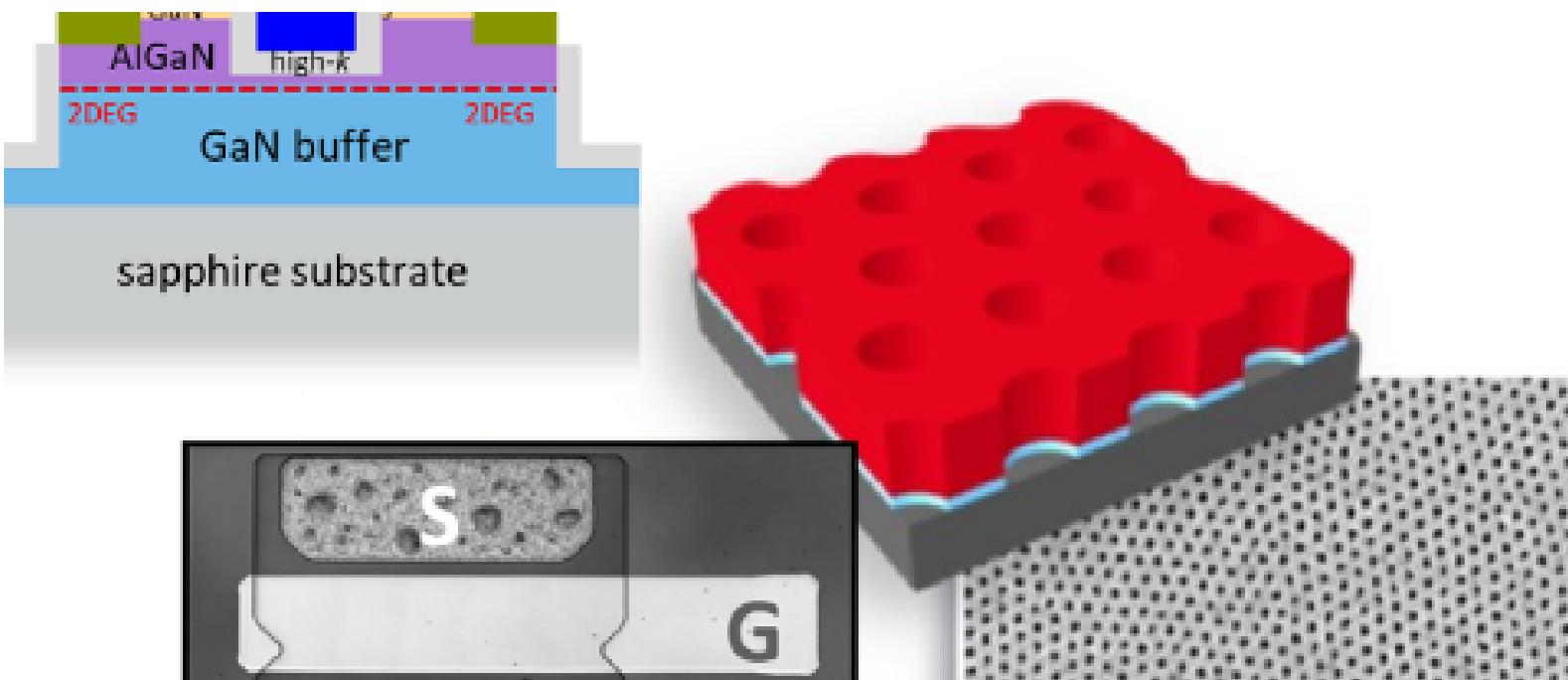
# Electronic Band engineering of GaN based MISHEMT devices by high-K dielectric integration and block-copolymer based atomic layer processing

[Prof. Dr. Johannes Heitmann](#)

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Institut für Angewandte Physik, TU Bergakademie Freiberg and Fraunhofer THM Freiberg (Germania)





GaN based devices are one of the main candidates for current power electronics and RF applications [1,2]. For optimizing device performance, a detailed understanding of the defects contained in the material and the passivation capability of dielectric layers, i.e., the interfacial defect states formed, is mandatory. Here, we will focus on the surface defect passivation and gate leakage current reduction by introducing thin dielectric films as gate insulator in a so-called MISHEMT (metal insulator semiconductor high electron mobility transistors) device using different materials.

EVENTO APERTO A:

Docenti | Teachers, Borsisti | Research Fellows, Assegnisti | Postdoctoral researcher, Dottorandi | PhD students, Studenti | Students

SEMINARIO IN LINGUA: INGLESE | ENGLISH

